

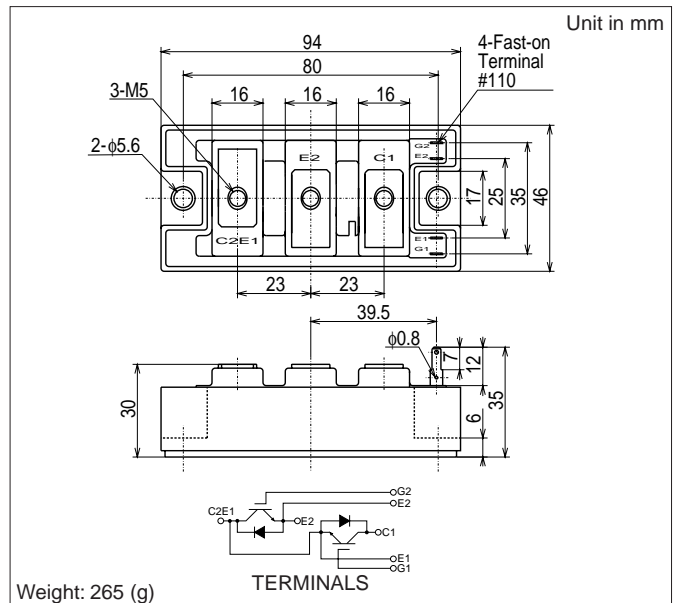
MBM300GS6AW

Silicon N-channel IGBT

OUTLINE DRAWING

FEATURES

- * High speed and low saturation voltage.
- * low noise due to built-in free-wheeling diode - ultra soft fast recovery diode(USFD).
- * Isolated head sink (terminal to base).



ABSOLUTE MAXIMUM RATINGS (T_c=25°C)

Item	Symbol	Unit	MBM300GS6AW
Collector Emitter Voltage	V _{CES}	V	600
Gate Emitter Voltage	V _{GES}	V	±20
Collector Current	DC	I _C	300
	1ms	I _{Cp}	600
Forward Current	DC	I _F	300 (1)
	1ms	I _{FM}	600
Collector Power Dissipation	P _c	W	800
Junction Temperature	T _j	°C	-40 ~ +150
Storage Temperature	T _{stg}	°C	-40 ~ +125
Isolation Voltage	V _{ISO}	V _{RMS}	2,500(AC 1 minute)
Screw Torque	Terminals	-	1.96(20) (2)
	Mounting	-	1.96(20) (3)

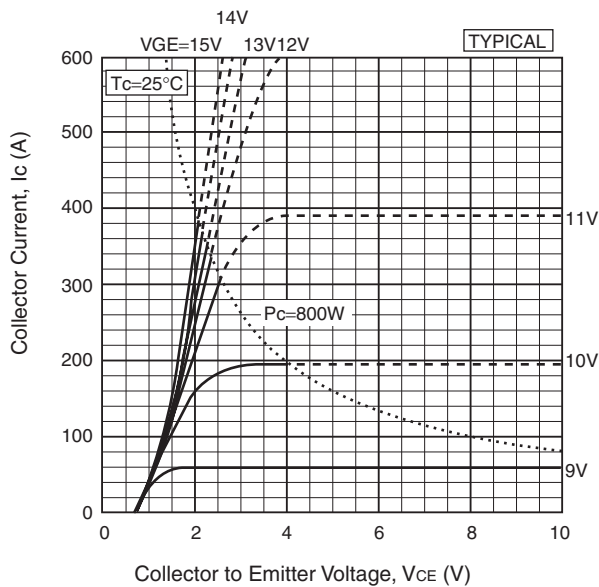
Notes:(1)RMS Current of Diode 90Arms max.

(2)(3)Recommended Value 1.67N.m(17kgf.cm)

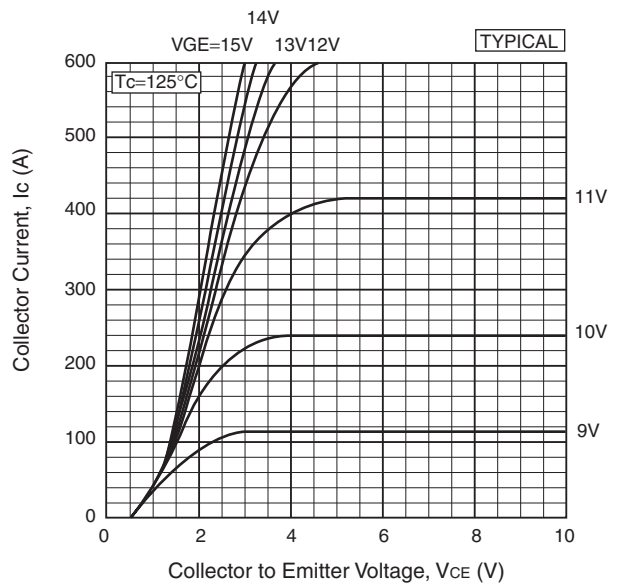
CHARACTERISTICS (T_c=25°C)

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Collector Emitter Cut-Off Current	I _{CES}	mA	-	-	1.0	V _{CE} =600V, V _{GE} =0V
Gate Emitter Leakage Current	I _{GES}	nA	-	-	±500	V _{GE} =±20V, V _{CE} =0V
Collector Emitter Saturation Voltage	V _{CE(sat)}	V	-	1.9	2.5	I _C =300A, V _{GE} =15V
Gate Emitter Threshold Voltage	V _{GE(TO)}	V	-	-	10	V _{CE} =5V, I _C =300mA
Input Capacitance	C _{ies}	pF	-	15,000	-	V _{CE} =10V, V _{GE} =0V, f=1MHz
Switching Times	Rise Time	t _r	-	0.25	0.5	V _{CC} =300V
	Turn On Time	t _{on}	-	0.35	0.7	R _L =1.0Ω
	Fall Time	t _f	-	0.25	0.35	R _G =8.2Ω (4)
	Turn Off Time	t _{off}	-	0.8	1.1	V _{GE} =±15V
Peak Forward Voltage Drop	V _{FM}	V	-	2.2	3.0	I _F =300A, V _{GE} =0V
Reverse Recovery Time	t _{rr}	μs	-	-	0.3	I _F =300A, V _{GE} =-10V, di/dt=300A/μs
Thermal Impedance	IGBT	R _{th(j-c)}	°C/W	-	0.156	Junction to case
	FWD	R _{th(j-c)}	°C/W	-	0.28	

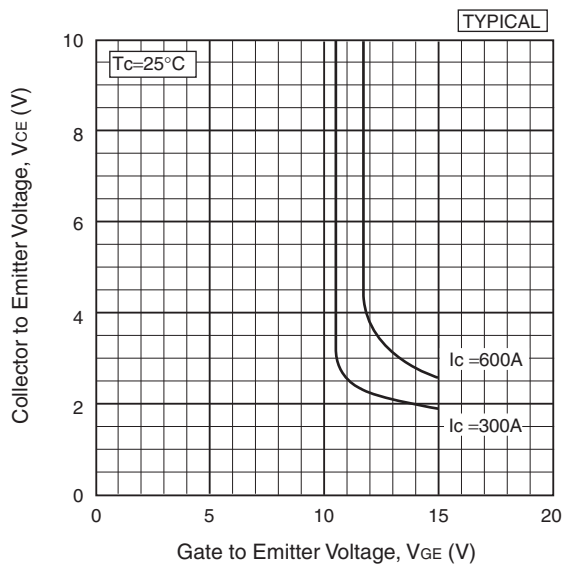
Notes:(4) R_G value is the test condition's value for decision of the switching times, not recommended value.Determine the suitable R_G value after the measurement of switching waveforms (overshoot voltage, etc.) with appliance mounted.



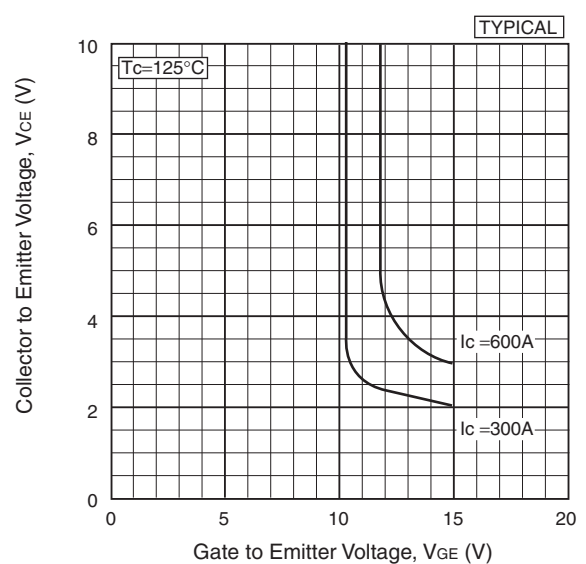
Collector current vs. Collector to Emitter voltage



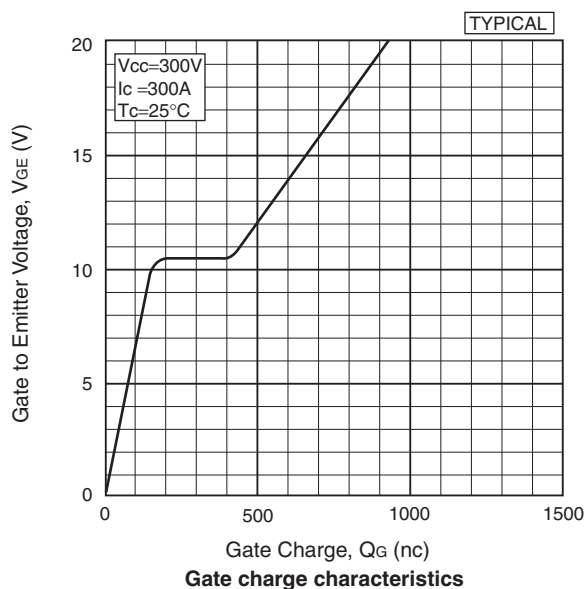
Collector current vs. Collector to Emitter voltage



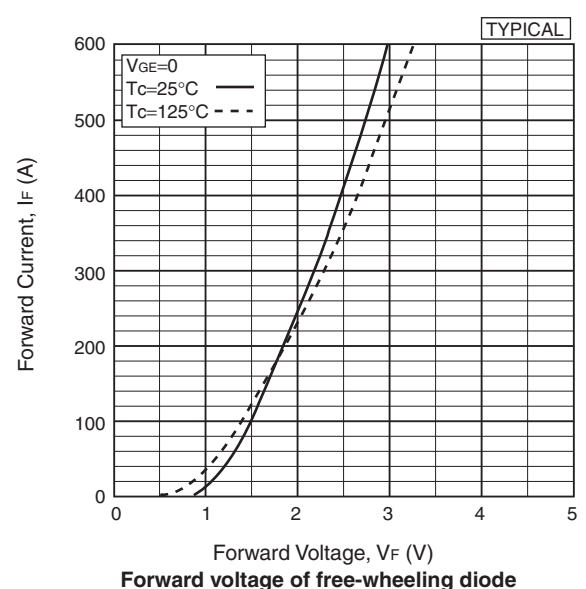
Collector to Emitter voltage vs. Gate to Emitter voltage



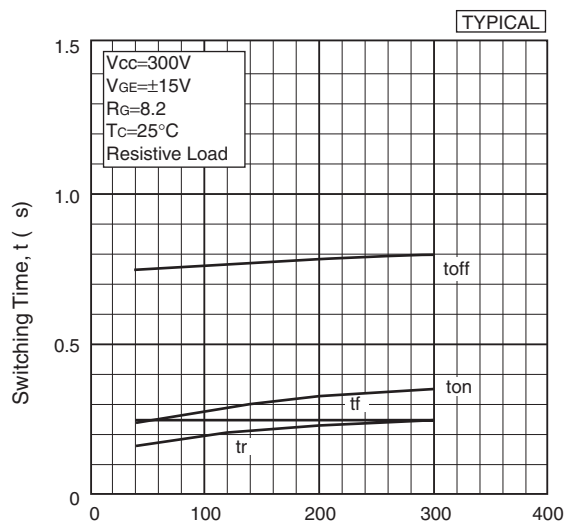
Collector to Emitter voltage vs. Gate to Emitter voltage



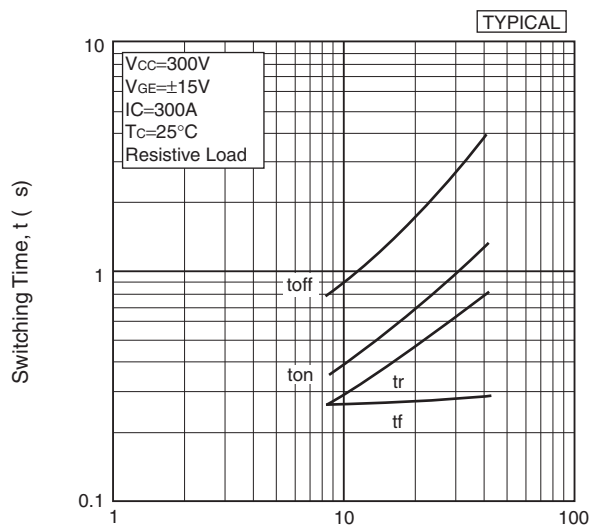
Gate charge characteristics



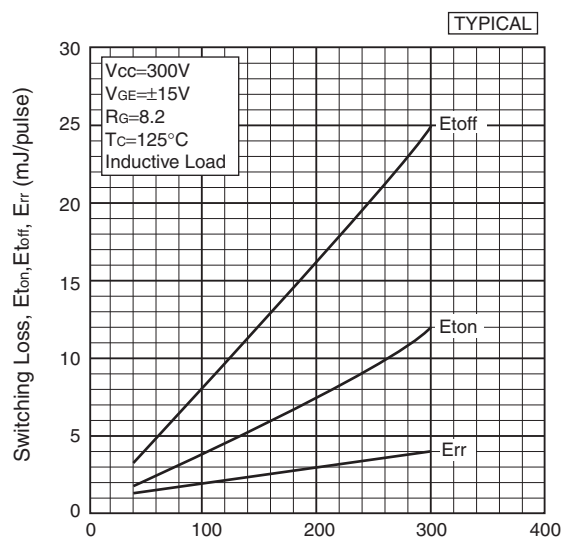
Forward voltage of free-wheeling diode



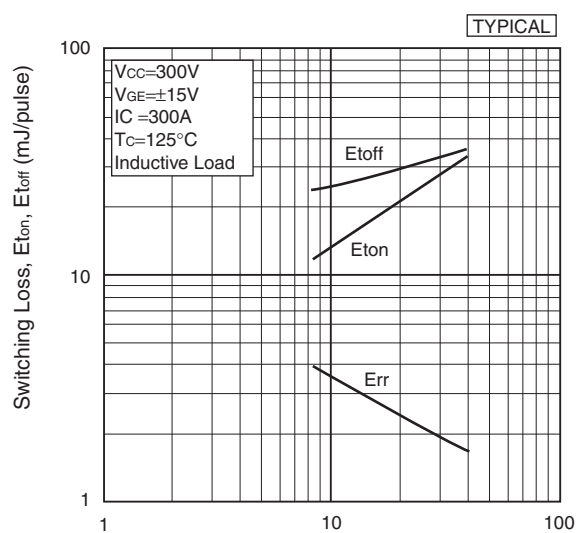
Switching time vs. Collector current



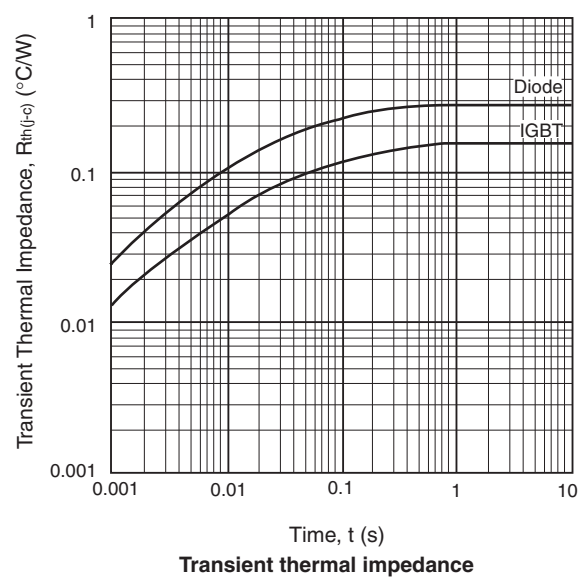
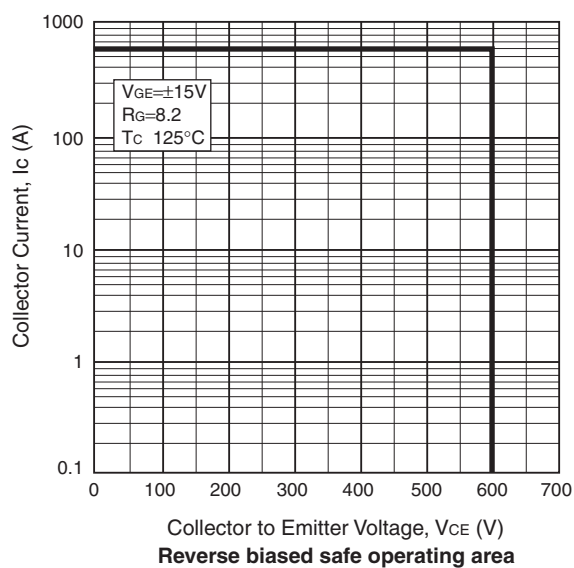
Switching time vs. Gate resistance



Switching loss vs. Collector current



Switching loss vs. Gate resistance



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